

Preliminary datasheet

EconoPIM™3 module with TRENCHSTOP™ IGBT7 and Emitter Controlled 7 diode and NTC

Features

- Electrical features
 - $V_{CES} = 1200\text{ V}$
 - $I_{C\text{ nom}} = 200\text{ A} / I_{CRM} = 400\text{ A}$
 - TRENCHSTOP™ IGBT7
 - Overload operation up to 175°C
 - Low V_{CESat}
- Mechanical features
 - Integrated NTC temperature sensor
 - PressFIT contact technology
 - Copper base plate
 - Al_2O_3 substrate with low thermal resistance



Typical appearance

Potential applications

- Auxiliary inverters
- Motor drives
- Servo drives

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description

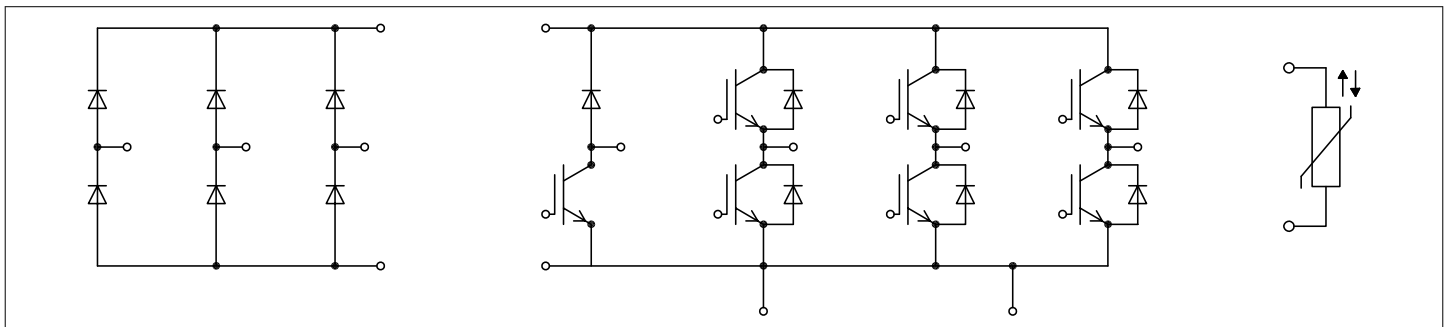


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1 Package

1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50 \text{ Hz}$, $t = 1 \text{ min}$	2.5	kV
Material of module baseplate			Cu	
Internal Isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Creepage distance	d_{Creep}	terminal to heatsink	10.0	mm
Clearance	d_{Clear}	terminal to heatsink	7.5	mm
Comparative tracking index	CTI		> 200	
RTI Elec.	RTI	housing	140	°C

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	L_{SCE}			25		nH
Module lead resistance, terminals - chip	$R_{AA'+CC'}$	$T_C = 25^\circ\text{C}$, per switch		1.1		mΩ
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_C = 25^\circ\text{C}$, per switch		1.6		mΩ
Storage temperature	T_{stg}		-40		125	°C
Mounting torque for modul mounting	M	- Mounting according to valid application note	M5, Screw	3	6	Nm
Weight	G			300		g

Note: The current under continuous operation is limited to 50A rms per connector pin.

2 IGBT, Inverter

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Collector-emitter voltage	V_{CES}	$T_{vj} = 25^\circ\text{C}$	1200	V
Continous DC collector current	I_{CDC}	$T_{vj \text{ max}} = 175^\circ\text{C}$ $T_C = 70^\circ\text{C}$	200	A
Repetitive peak collector current	I_{CRM}	$t_p = 1 \text{ ms}$	400	A
Gate-emitter peak voltage	V_{GES}		±20	V

Table 4 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 200\ A, V_{GE} = 15\ V$	$T_{vj} = 25\ ^\circ C$		1.55	TBD	V
			$T_{vj} = 125\ ^\circ C$		1.69		
			$T_{vj} = 175\ ^\circ C$		1.77		
Gate threshold voltage	V_{GEth}	$I_C = 4.6\ mA, V_{CE} = V_{GE}, T_{vj} = 25\ ^\circ C$		5.15	5.80	6.45	V
Gate charge	Q_G	$V_{GE} = \pm 15\ V, V_{CE} = 600\ V$			3.34		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\ ^\circ C$			0.75		Ω
Input capacitance	C_{ies}	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$			40.3		nF
Reverse transfer capacitance	C_{res}	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$			0.14		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 1200\ V, V_{GE} = 0\ V$	$T_{vj} = 25\ ^\circ C$			0.02	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\ V, V_{GE} = 20\ V, T_{vj} = 25\ ^\circ C$				100	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 200\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 2.7\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.203		μs
			$T_{vj} = 125\ ^\circ C$		0.226		
			$T_{vj} = 175\ ^\circ C$		0.239		
Rise time (inductive load)	t_r	$I_C = 200\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 2.7\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.094		μs
			$T_{vj} = 125\ ^\circ C$		0.097		
			$T_{vj} = 175\ ^\circ C$		0.099		
Turn-off delay time (inductive load)	t_{doff}	$I_C = 200\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 2.7\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.351		μs
			$T_{vj} = 125\ ^\circ C$		0.414		
			$T_{vj} = 175\ ^\circ C$		0.433		
Fall time (inductive load)	t_f	$I_C = 200\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 2.7\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.103		μs
			$T_{vj} = 125\ ^\circ C$		0.198		
			$T_{vj} = 175\ ^\circ C$		0.262		
Turn-on energy loss per pulse	E_{on}	$I_C = 200\ A, V_{CE} = 600\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Gon} = 2.7\ \Omega, di/dt = 2050\ A/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$		25.1		mJ
			$T_{vj} = 125\ ^\circ C$		38.3		
			$T_{vj} = 175\ ^\circ C$		45.9		
Turn-off energy loss per pulse	E_{off}	$I_C = 200\ A, V_{CE} = 600\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Goff} = 2.7\ \Omega, dv/dt = 3250\ V/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$		12.9		mJ
			$T_{vj} = 125\ ^\circ C$		20.5		
			$T_{vj} = 175\ ^\circ C$		23.8		
SC data	I_{SC}	$V_{GE} \leq 15\ V, V_{CC} = 800\ V, V_{CEmax} = V_{CES} - L_{sCE} * di/dt$	$t_p \leq 8\ \mu s, T_{vj} = 150\ ^\circ C$		640		A
			$t_p \leq 7\ \mu s, T_{vj} = 175\ ^\circ C$		600		

Table 4 Characteristic values (continued)

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Thermal resistance, junction to case	R_{thJC}	per IGBT			0.231	K/W
Thermal resistance, case to heatsink	R_{thCH}	per IGBT, $\lambda_{grease} = 1 \text{ W}/(\text{m}^2\text{K})$		0.0670		K/W
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		175	°C

Note: $T_{vj\text{ op}} > 150^\circ\text{C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

3 Diode, Inverter

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} = 25^\circ\text{C}$	1200	V	
Continuous DC forward current	I_F		200	A	
Repetitive peak forward current	I_{FRM}	$t_P = 1 \text{ ms}$	400	A	
I^2t - value	I^2t	$t_P = 10 \text{ ms}, V_R = 0 \text{ V}$	$T_{vj} = 125^\circ\text{C}$	3700	A^2s
			$T_{vj} = 175^\circ\text{C}$	3050	

Table 6 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Forward voltage	V_F	$I_F = 200 \text{ A}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25^\circ\text{C}$		1.72	TBD	V
			$T_{vj} = 125^\circ\text{C}$		1.59		
			$T_{vj} = 175^\circ\text{C}$		1.52		
Peak reverse recovery current	I_{RM}	$V_R = 600 \text{ V}, I_F = 200 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 2050 \text{ A}/\mu\text{s} (T_{vj} = 175^\circ\text{C})$	$T_{vj} = 25^\circ\text{C}$		79.6		A
			$T_{vj} = 125^\circ\text{C}$		105		
			$T_{vj} = 175^\circ\text{C}$		118		
Recovered charge	Q_r	$V_R = 600 \text{ V}, I_F = 200 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 2050 \text{ A}/\mu\text{s} (T_{vj} = 175^\circ\text{C})$	$T_{vj} = 25^\circ\text{C}$		15.7		μC
			$T_{vj} = 125^\circ\text{C}$		27.7		
			$T_{vj} = 175^\circ\text{C}$		35.6		

Table 6 Characteristic values (continued)

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Reverse recovery energy	E_{rec}	$V_R = 600\text{ V}$, $I_F = 200\text{ A}$, $V_{GE} = -15\text{ V}$, $-di_F/dt = 2050\text{ A}/\mu\text{s}$ ($T_{vj} = 175\text{ °C}$)	$T_{vj} = 25\text{ °C}$	4.85		mJ
			$T_{vj} = 125\text{ °C}$	9.64		
			$T_{vj} = 175\text{ °C}$	12.2		
Thermal resistance, junction to case	R_{thJC}	per diode			0.376	K/W
Thermal resistance, case to heatsink	R_{thCH}	per diode, $\lambda_{grease} = 1\text{ W}/(\text{m}^*\text{K})$		0.0730		K/W
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		175	°C

Note: $T_{vj\text{ op}} > 150\text{ °C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

4 Diode, Rectifier

Table 7 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} = 25\text{ °C}$	1600	V	
Maximum RMS forward current per chip	I_{FRMSM}	$T_C = 110\text{ °C}$	150	A	
Maximum RMS current at rectifier output	I_{RMSM}	$T_C = 110\text{ °C}$	150	A	
Surge forward current	I_{FSM}	$t_p = 10\text{ ms}$	$T_{vj} = 25\text{ °C}$	1800	A
			$T_{vj} = 150\text{ °C}$	1600	
I^2t - value	I^2t	$t_p = 10\text{ ms}$	$T_{vj} = 25\text{ °C}$	16200	A^2s
			$T_{vj} = 150\text{ °C}$	12800	

Table 8 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 200\text{ A}$, $T_{vj} = 150\text{ °C}$		1.01		V
Reverse current	I_r	$T_{vj} = 150\text{ °C}$, $V_R = 1600\text{ V}$		1.4		mA
Thermal resistance, junction to case	R_{thJC}	per diode			0.278	K/W
Thermal resistance, case to heatsink	R_{thCH}	per diode, $\lambda_{grease} = 1\text{ W}/(\text{m}^*\text{K})$		0.0690		K/W

Table 8 Characteristic values (continued)

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Temperature under switching conditions	$T_{vj, op}$		-40		150	°C

5 IGBT, Brake-Chopper

Table 9 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Collector-emitter voltage	V_{CES}	$T_{vj} = 25\text{ °C}$	1200	V
Continuous DC collector current	I_{CDC}	$T_{vj\ max} = 175\text{ °C}$ $T_C = 75\text{ °C}$	150	A
Repetitive peak collector current	I_{CRM}	$t_p = 1\text{ ms}$	300	A
Gate-emitter peak voltage	V_{GES}		±20	V

Table 10 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 150\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25\text{ °C}$	1.55	TBD	V
			$T_{vj} = 125\text{ °C}$	1.69		
			$T_{vj} = 175\text{ °C}$	1.77		
Gate threshold voltage	V_{GEth}	$I_C = 3.5\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25\text{ °C}$	5.15	5.80	6.45	V
Gate charge	Q_G	$V_{GE} = \pm 15\text{ V}, V_{CE} = 600\text{ V}$		2.5		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\text{ °C}$		1		Ω
Input capacitance	C_{ies}	$f = 100\text{ kHz}, T_{vj} = 25\text{ °C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		30.1		nF
Reverse transfer capacitance	C_{res}	$f = 100\text{ kHz}, T_{vj} = 25\text{ °C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		0.105		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}$			0.005	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25\text{ °C}$			100	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 150\text{ A}, V_{CE} = 600\text{ V}, V_{GE} = \pm 15\text{ V}, R_{Gon} = 5.6\text{ }\Omega$	$T_{vj} = 25\text{ °C}$	0.197		μs
			$T_{vj} = 125\text{ °C}$	0.208		
			$T_{vj} = 175\text{ °C}$	0.215		
Rise time (inductive load)	t_r	$I_C = 150\text{ A}, V_{CE} = 600\text{ V}, V_{GE} = \pm 15\text{ V}, R_{Gon} = 5.6\text{ }\Omega$	$T_{vj} = 25\text{ °C}$	0.085		μs
			$T_{vj} = 125\text{ °C}$	0.090		
			$T_{vj} = 175\text{ °C}$	0.093		

Table 10 Characteristic values (continued)

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Turn-off delay time (inductive load)	t_{doff}	$I_C = 150\text{ A}, V_{CE} = 600\text{ V}, V_{GE} = \pm 15\text{ V}, R_{Goff} = 5.6\ \Omega$	$T_{vj} = 25\text{ }^\circ\text{C}$	0.419		μs
			$T_{vj} = 125\text{ }^\circ\text{C}$	0.502		
			$T_{vj} = 175\text{ }^\circ\text{C}$	0.521		
Fall time (inductive load)	t_f	$I_C = 150\text{ A}, V_{CE} = 600\text{ V}, V_{GE} = \pm 15\text{ V}, R_{Goff} = 5.6\ \Omega$	$T_{vj} = 25\text{ }^\circ\text{C}$	0.113		μs
			$T_{vj} = 125\text{ }^\circ\text{C}$	0.208		
			$T_{vj} = 175\text{ }^\circ\text{C}$	0.272		
Turn-on energy loss per pulse	E_{on}	$I_C = 150\text{ A}, V_{CE} = 600\text{ V}, L_\sigma = 35\text{ nH}, V_{GE} = \pm 15\text{ V}, R_{Gon} = 5.6\ \Omega, di/dt = 1150\text{ A}/\mu\text{s} (T_{vj} = 175\text{ }^\circ\text{C})$	$T_{vj} = 25\text{ }^\circ\text{C}$	12.2		mJ
			$T_{vj} = 125\text{ }^\circ\text{C}$	19.1		
			$T_{vj} = 175\text{ }^\circ\text{C}$	23.1		
Turn-off energy loss per pulse	E_{off}	$I_C = 150\text{ A}, V_{CE} = 600\text{ V}, L_\sigma = 35\text{ nH}, V_{GE} = \pm 15\text{ V}, R_{Goff} = 5.6\ \Omega, dv/dt = 3100\text{ V}/\mu\text{s} (T_{vj} = 175\text{ }^\circ\text{C})$	$T_{vj} = 25\text{ }^\circ\text{C}$	10.5		mJ
			$T_{vj} = 125\text{ }^\circ\text{C}$	16.1		
			$T_{vj} = 175\text{ }^\circ\text{C}$	20.1		
SC data	I_{SC}	$V_{GE} \leq 15\text{ V}, V_{CC} = 800\text{ V}, V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$	$t_p \leq 8\ \mu\text{s}, T_{vj} = 150\text{ }^\circ\text{C}$	480		A
			$t_p \leq 7\ \mu\text{s}, T_{vj} = 175\text{ }^\circ\text{C}$	450		
Thermal resistance, junction to case	R_{thJC}	per IGBT			0.290	K/W
Thermal resistance, case to heatsink	R_{thCH}	per IGBT, $\lambda_{grease} = 1\text{ W}/(\text{m}^2\text{K})$		0.0700		K/W
Temperature under switching conditions	T_{vjop}		-40		175	$^\circ\text{C}$

Note: $T_{vjop} > 150\text{ }^\circ\text{C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

6 Diode, Brake-Chopper

Table 11 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} = 25\text{ }^\circ\text{C}$	1200	V
Continuous DC forward current	I_F		75	A
Repetitive peak forward current	I_{FRM}	$t_p = 1\text{ ms}$	150	A

Table 11 Maximum rated values (continued)

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
I ² t - value	I ² t	t _p = 10 ms, V _R = 0 V	T _{vj} = 125 °C	450		A ² s
			T _{vj} = 175 °C	370		

Table 12 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V _F	I _F = 75 A, V _{GE} = 0 V	T _{vj} = 25 °C	1.72	TBD	V
			T _{vj} = 125 °C	1.59		
			T _{vj} = 175 °C	1.52		
Peak reverse recovery current	I _{RM}	V _R = 600 V, I _F = 75 A, V _{GE} = -15 V, -di _F /dt = 1050 A/μs (T _{vj} = 175 °C)	T _{vj} = 25 °C	38.2		A
			T _{vj} = 125 °C	50.9		
			T _{vj} = 175 °C	58.9		
Recovered charge	Q _r	V _R = 600 V, I _F = 75 A, V _{GE} = -15 V, -di _F /dt = 1050 A/μs (T _{vj} = 175 °C)	T _{vj} = 25 °C	5.43		μC
			T _{vj} = 125 °C	10.4		
			T _{vj} = 175 °C	14.1		
Reverse recovery energy	E _{rec}	V _R = 600 V, I _F = 75 A, V _{GE} = -15 V, -di _F /dt = 1050 A/μs (T _{vj} = 175 °C)	T _{vj} = 25 °C	10		mJ
			T _{vj} = 125 °C	10		
			T _{vj} = 175 °C	10		
Thermal resistance, junction to case	R _{thJC}	per diode			0.728	K/W
Thermal resistance, case to heatsink	R _{thCH}	per diode, λ _{grease} = 1 W/(m*K)		0.0870		K/W
Temperature under switching conditions	T _{vj op}		-40		175	°C

Note: T_{vj op} > 150°C is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

7 NTC-Thermistor

Table 13 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R ₂₅	T _{NTC} = 25 °C		5		kΩ
Deviation of R ₁₀₀	ΔR/R	T _{NTC} = 100 °C, R ₁₀₀ = 493 Ω	-5		5	%
Power dissipation	P ₂₅	T _{NTC} = 25 °C			20	mW

Table 13 **Characteristic values (continued)**

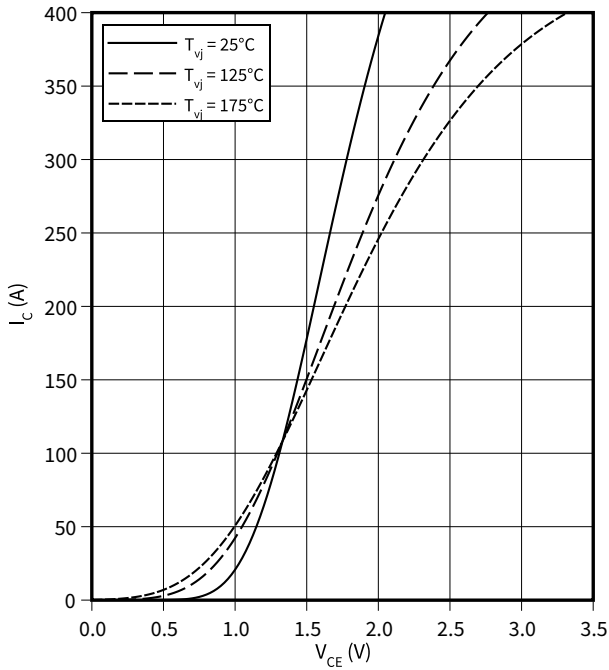
Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2 - 1/(298,15 \text{ K}))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2 - 1/(298,15 \text{ K}))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2 - 1/(298,15 \text{ K}))]$		3433		K

Note: *Specification according to the valid application note.*

8 Characteristics diagrams

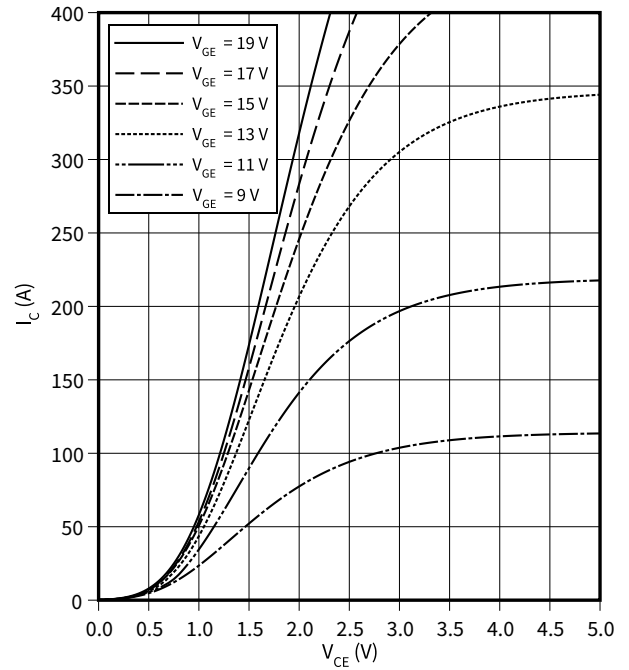
output characteristic (typical), IGBT, Inverter

$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



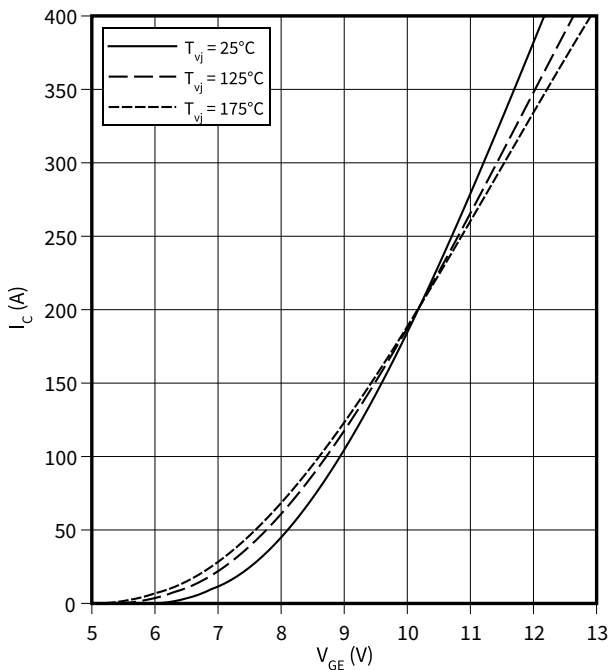
output characteristic (typical), IGBT, Inverter

$I_C = f(V_{CE})$
 $T_{vj} = 175\text{ °C}$



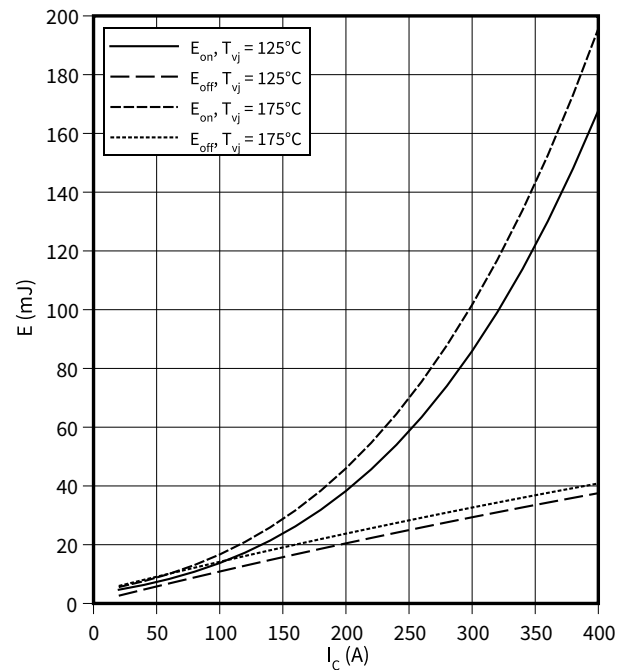
transfer characteristic (typical), IGBT, Inverter

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



switching losses (typical), IGBT, Inverter

$E = f(I_C)$
 $R_{Goff} = 2.7\ \Omega, R_{Gon} = 2.7\ \Omega, V_{CE} = 600\text{ V}, V_{GE} = \pm 15\text{ V}$

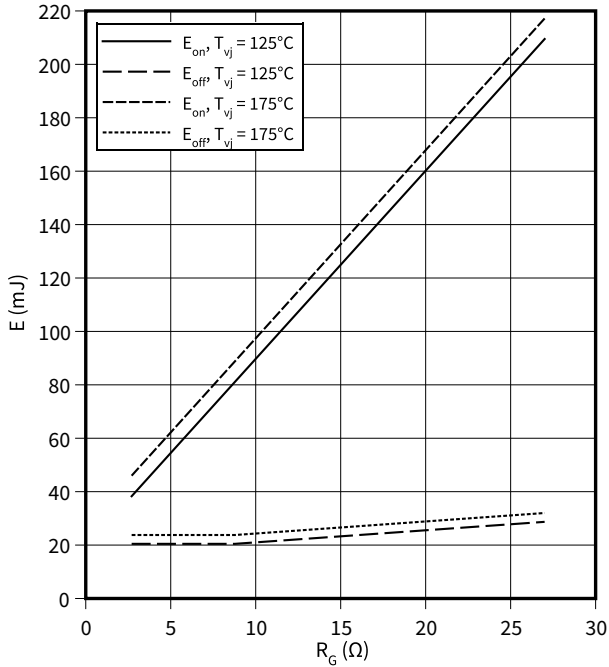


8 Characteristics diagrams

switching losses (typical), IGBT, Inverter

$E = f(R_G)$

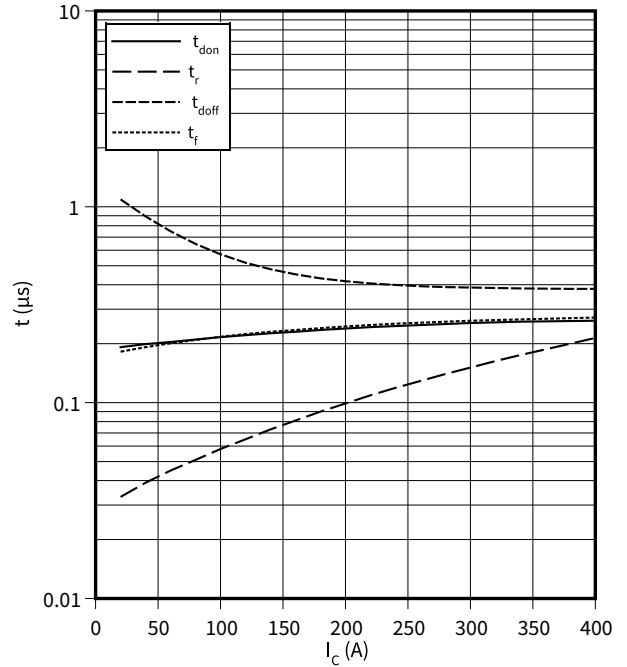
$I_C = 200 \text{ A}, V_{CE} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}$



switching times (typical), IGBT, Inverter

$t = f(I_C)$

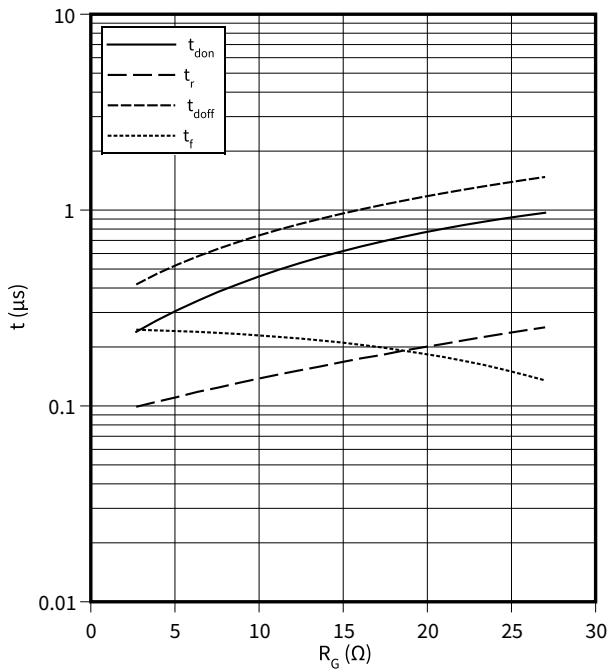
$R_{Goff} = 2.7 \Omega, R_{Gon} = 2.7 \Omega, V_{CE} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}, T_{vj} = 175 \text{ °C}$



switching times (typical), IGBT, Inverter

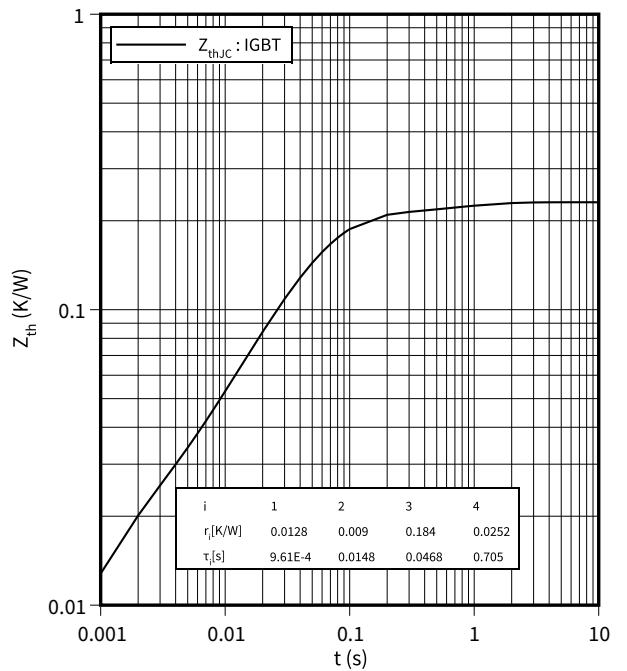
$t = f(R_G)$

$I_C = 200 \text{ A}, V_{CE} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}, T_{vj} = 175 \text{ °C}$



transient thermal impedance, IGBT, Inverter

$Z_{th} = f(t)$

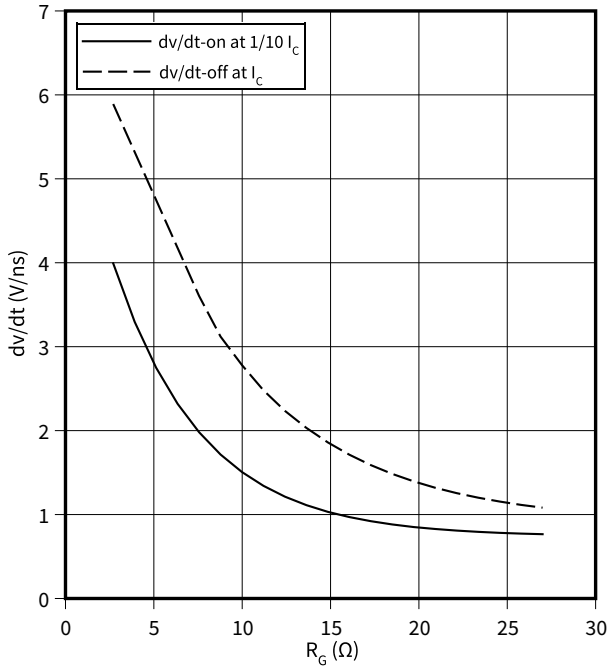


8 Characteristics diagrams

Voltage slope (typical), IGBT, Inverter

$dv/dt = f(R_G)$

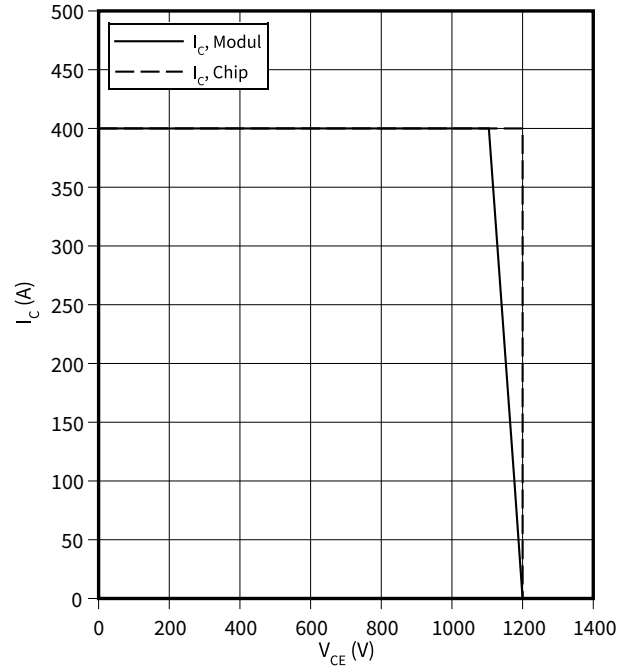
$I_C = 200\text{ A}$, $V_{CE} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $T_{vj} = 25\text{ }^\circ\text{C}$



reverse bias safe operating area (RBSOA), IGBT, Inverter

$I_C = f(V_{CE})$

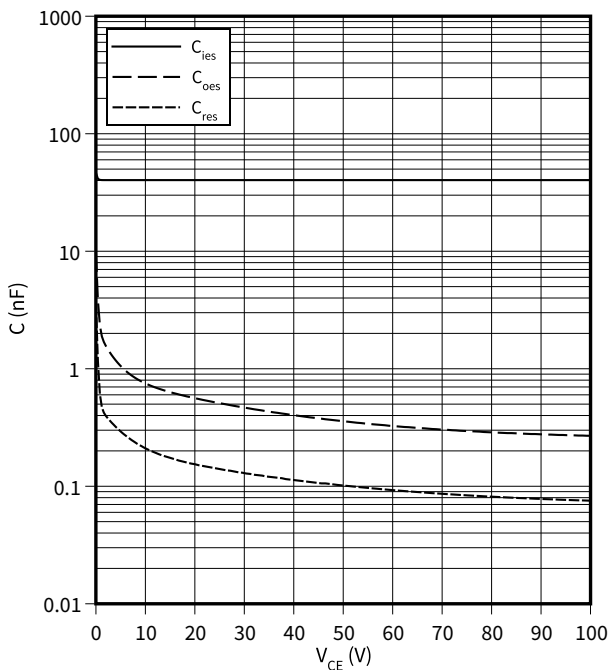
$R_{Goff} = 2.7\text{ } \Omega$, $V_{GE} = \pm 15\text{ V}$, $T_{vj} = 175\text{ }^\circ\text{C}$



capacity characteristic (typical), IGBT, Inverter

$C = f(V_{CE})$

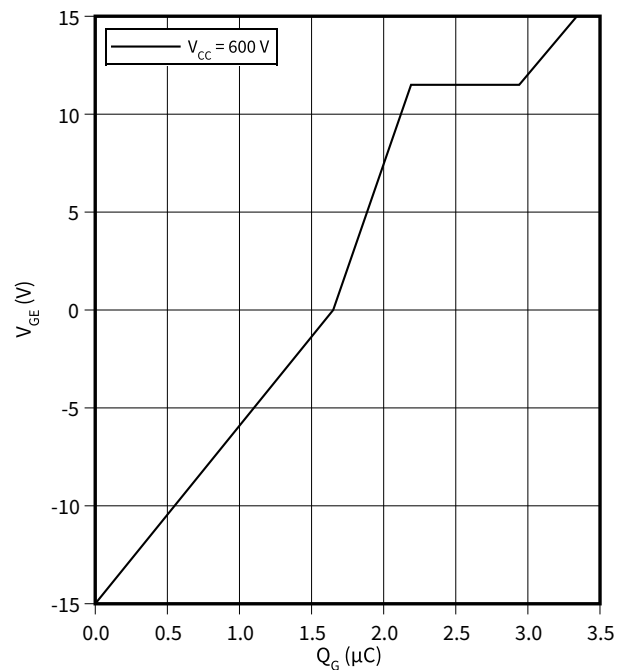
$f = 100\text{ kHz}$, $V_{GE} = 0\text{ V}$, $T_{vj} = 25\text{ }^\circ\text{C}$



gate charge characteristic (typical), IGBT, Inverter

$V_{GE} = f(Q_G)$

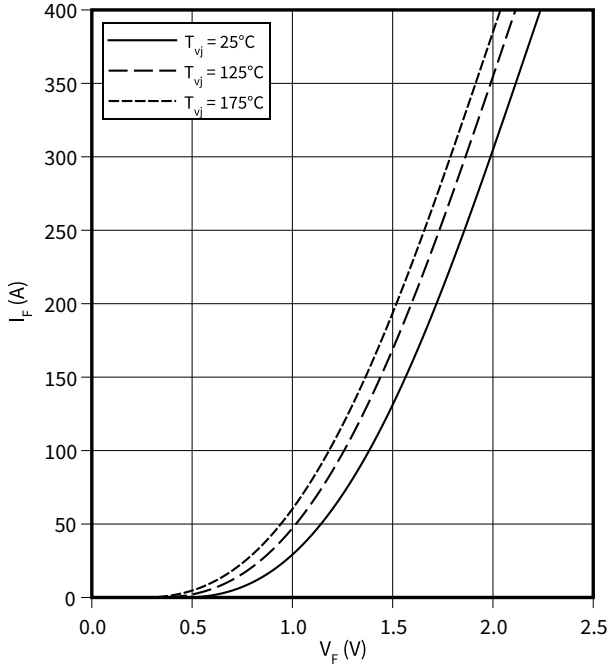
$I_C = 200\text{ A}$, $T_{vj} = 25\text{ }^\circ\text{C}$



8 Characteristics diagrams

forward characteristic (typical), Diode, Inverter

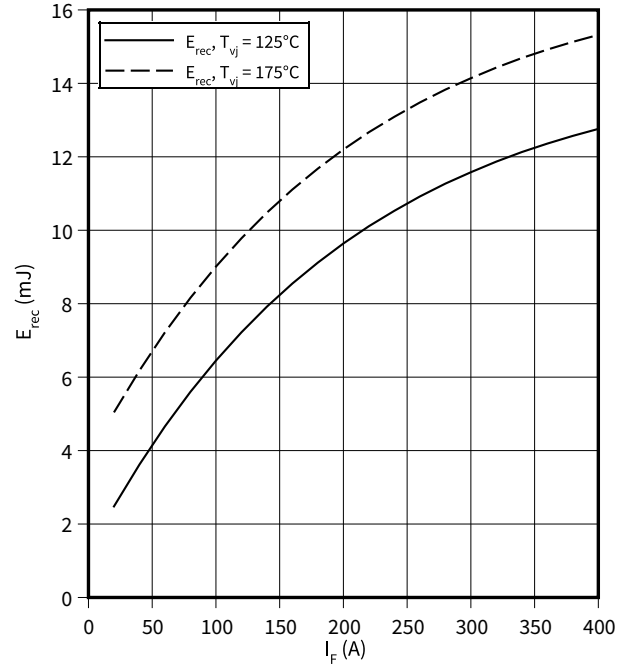
$I_F = f(V_F)$



switching losses (typical), Diode, Inverter

$E_{rec} = f(I_F)$

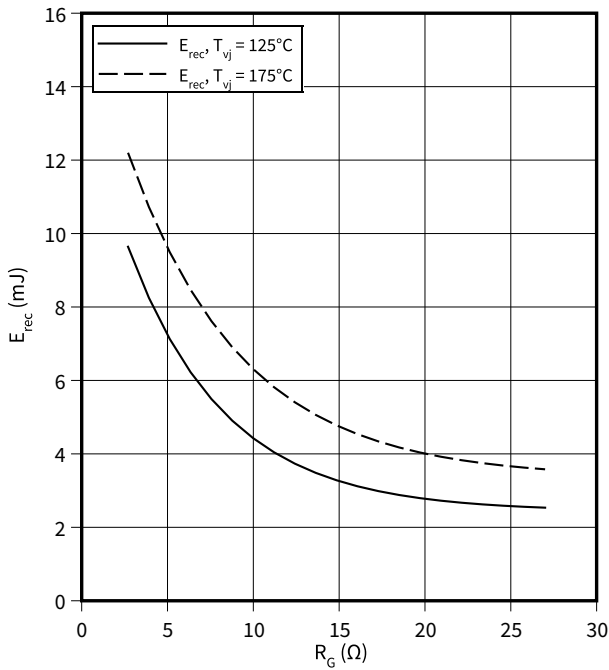
$R_{Gon} = 2.7 \Omega, V_{CE} = 600 V$



switching losses (typical), Diode, Inverter

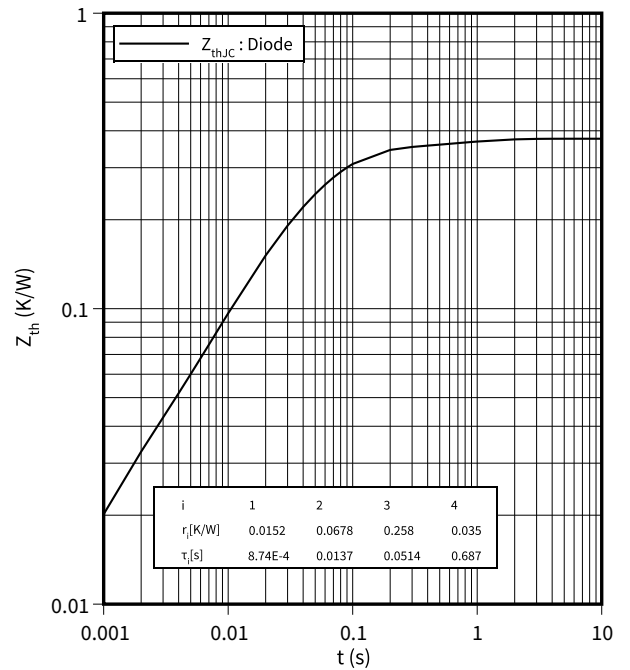
$E_{rec} = f(R_G)$

$V_{CE} = 600 V, I_F = 200 A$



transient thermal impedance, Diode, Inverter

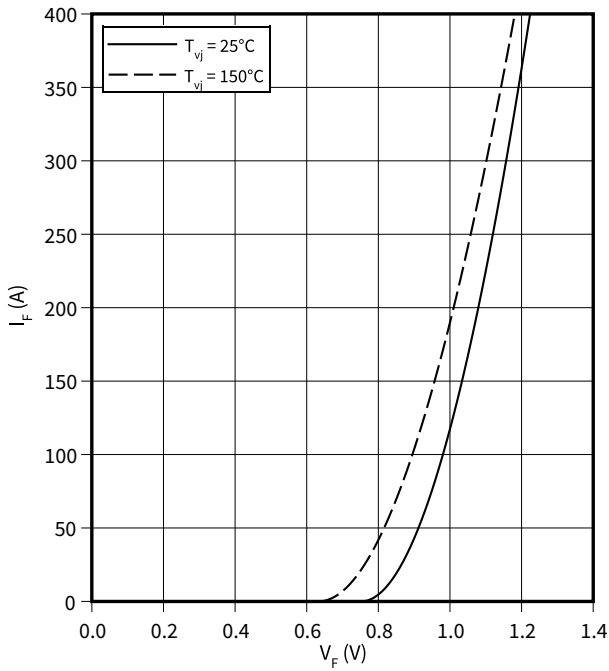
$Z_{th} = f(t)$



8 Characteristics diagrams

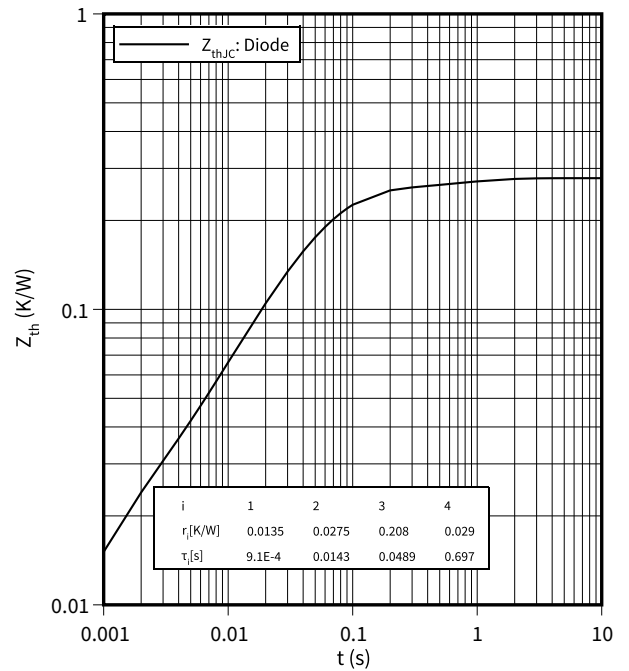
forward characteristic (typical), Diode, Rectifier

$I_F = f(V_F)$



transient thermal impedance, Diode, Rectifier

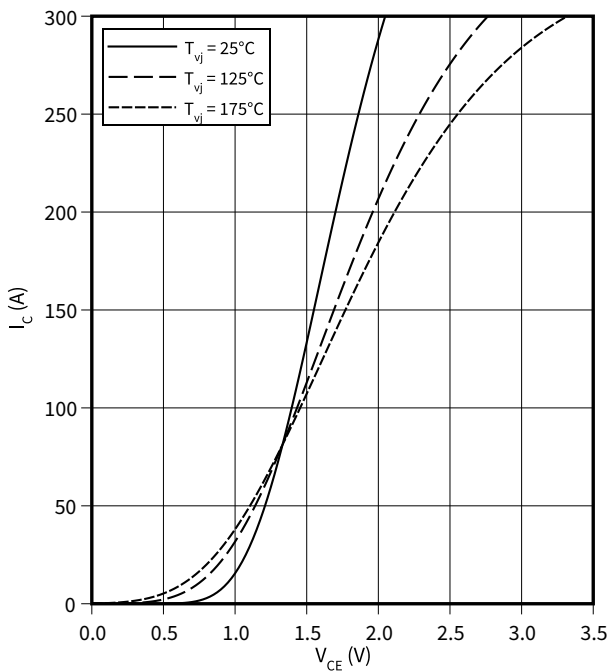
$Z_{th} = f(t)$



output characteristic (typical), IGBT, Brake-Chopper

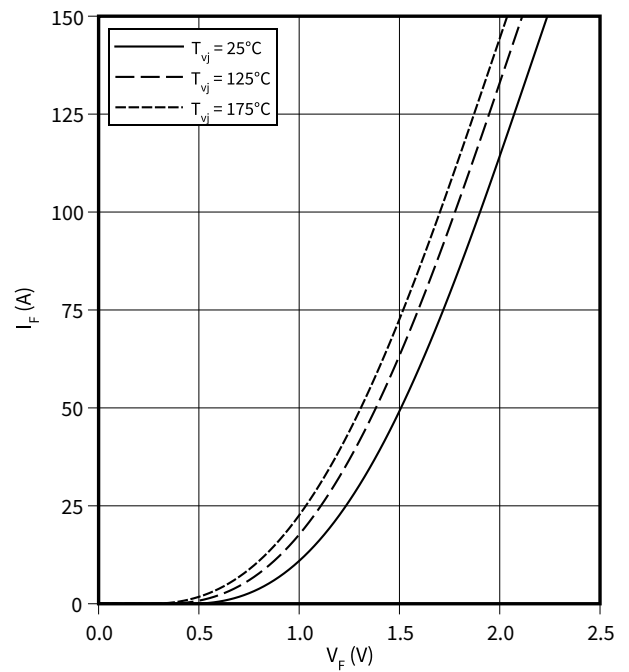
$I_C = f(V_{CE})$

$V_{GE} = 15 \text{ V}$



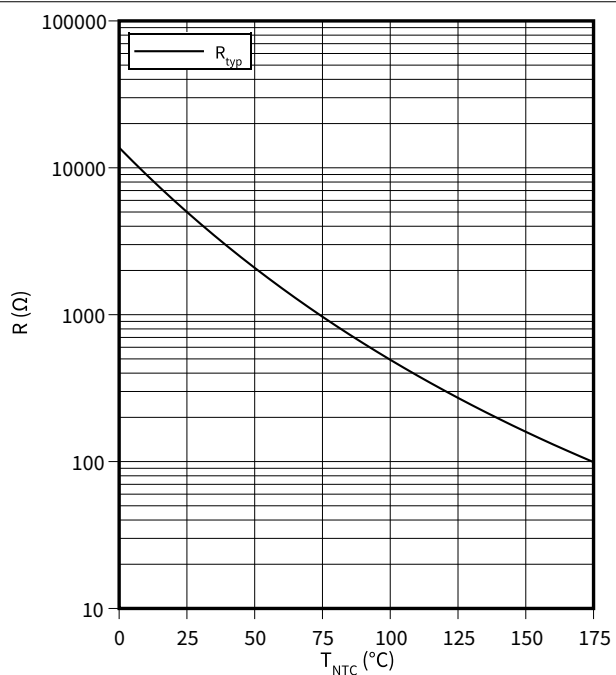
forward characteristic (typical), Diode, Brake-Chopper

$I_F = f(V_F)$



temperature characteristic (typical), NTC-Thermistor

$$R = f(T_{NTC})$$



9 Circuit diagram

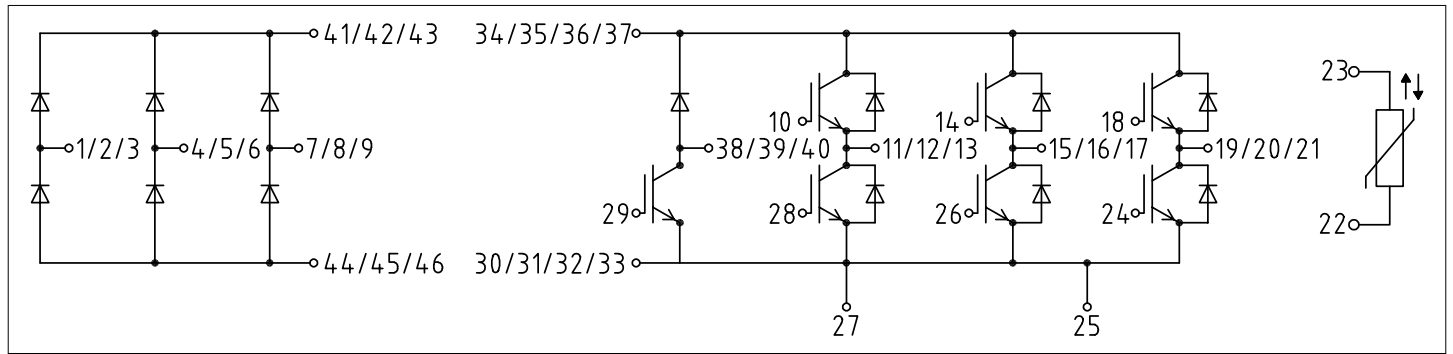


Figure 2

10 Package outlines

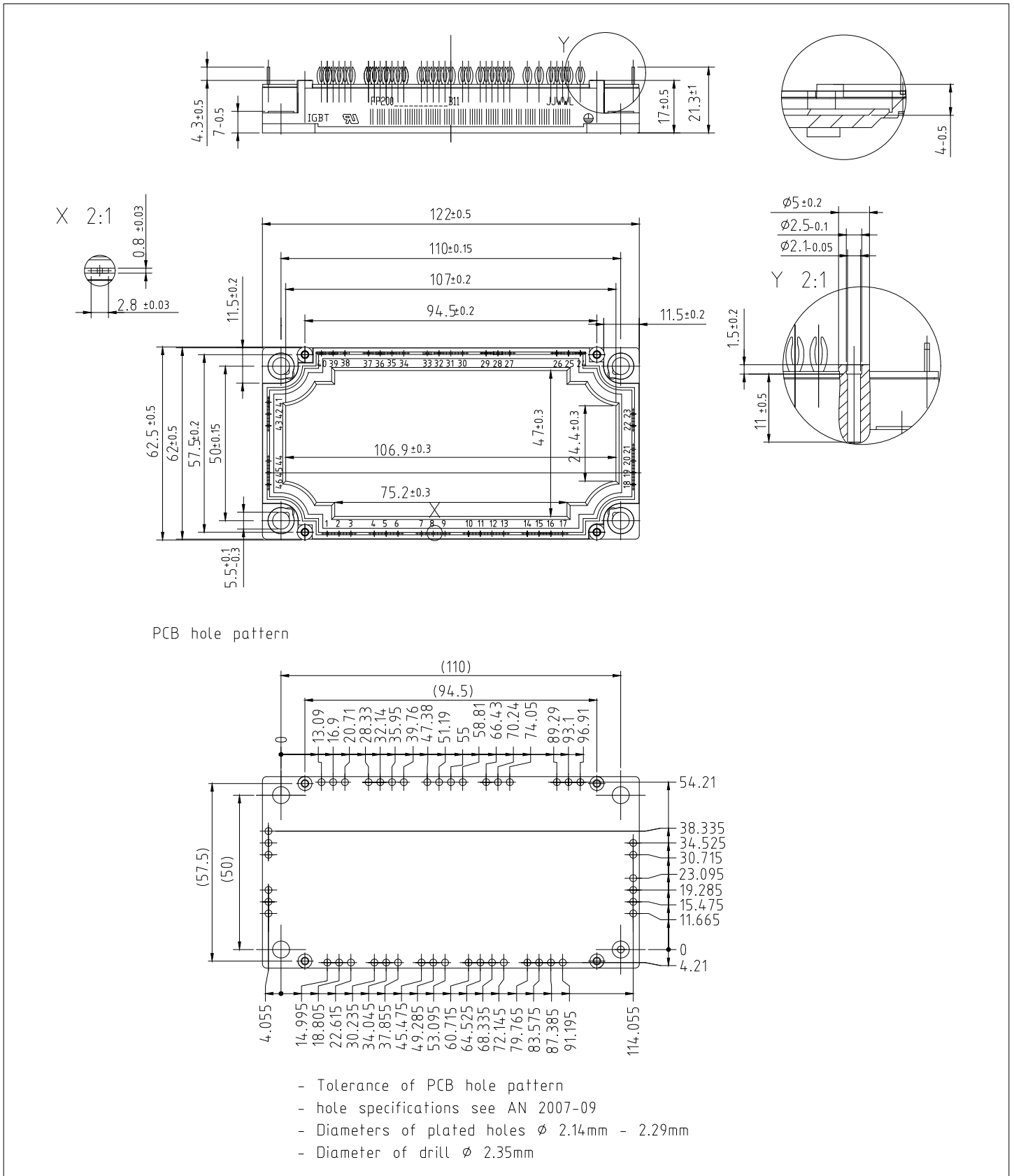


Figure 3

Revision history

Revision history

Document revision	Date of release	Description of changes
0.10	2021-08-26	Initial version

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Edition 2021-08-26

Published by

Infineon Technologies AG

81726 Munich, Germany

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Document reference

IFX-ABB747-001

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